

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1420	(hig-k or (high near k) or ((high near dielectric) near2 film)) same (gate adj electrode) same (gate near (insulating or dielectric or insulation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:15
L2	144	(hig-k or (high near k) or ((high near dielectric) near2 film)) same (gate adj electrode) same (gate near (insulating or dielectric or insulation)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:17
L3	1	(hig-k or (high near k) or ((high near dielectric) near2 film)) same (gate adj electrode) same (gate near (insulating or dielectric or insulation) same (express or expressed or expression or formula or relationship)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:17
L4	19	(hig-k or (high near k) or ((high near dielectric) near2 film)) same (gate adj electrode) same (gate near (insulating or dielectric or insulation) same (express or expressed or expression or formula or relationship))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:18
L5	25	(hig-k or (high near k) or ((high near dielectric) near2 film)) same (gate adj electrode) same (gate near (insulating or dielectric or insulation) same (express or expressed or expression or formula or relationship or inequality or satisfy or satisfying or satisfied))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:21
L6	647	(257/410 or 257/200 or 257/52 or 257/413 or 257/411 or 257/412 or 257/310) and (hig-k or (high near k) or ((high near dielectric) near2 film)) and (gate adj electrode) and (gate near (insulating or dielectric or insulation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:23
L7	602	(257/410 or 257/200 or 257/52 or 257/413 or 257/411 or 257/412 or 257/310) and ((hig-k or (high near k) or ((high near dielectric) near2 (layer or film)) and (gate adj electrode) and (gate near (insulating or dielectric or insulation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:24

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L8	224	(257/410 or 257/200 or 257/52 or 257/413 or 257/411 or 257/412 or 257/310) and ((hig-k or (high near k) or ((high near dielectric))) near2 (layer or film)).ti,ab,clm. and (gate adj electrode) and (gate near (insulating or dielectric or insulation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:25
L9	6	(257/410 or 257/200 or 257/52 or 257/413 or 257/411 or 257/412 or 257/310) and (((hig-k or (high near k) or ((high near dielectric))) near2 (layer or film)) near10 (satisfy or formula or satisfies or satisfying or expression or expressed or expressing or inequality or relationship)).ti,ab,clm. and (gate adj electrode) and (gate near (insulating or dielectric or insulation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/11 16:27